

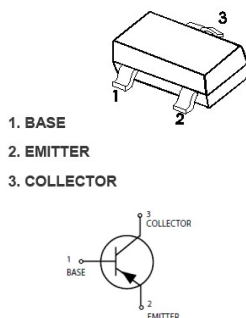
SS8550 TRANSISTOR(PNP)

Rev.2.0

SOT-23

SOT-23 贴片塑封三极管

SOT-23 Plastic-Encapsulate Transistors



Marking: Y2

特征 Features

- 与 SS8050 配对; Complementary to SS8050
- 最大功率耗散 300mW; Power Dissipation of 300mW
- 高稳定性和可靠性。High Stability and High Reliability

机械数据 Mechanical Data

- 封装: SOT-23 封装 SOT-23 Small Outline Plastic Package
- 环氧树脂 UL 易燃等级 Epoxy UL: 94V-0
- 安装位置: 任意 Mounting Position: Any

极限值和温度特性(TA = 25°C 除非另有规定)

Maximum Ratings & Thermal Characteristics (Ratings at 25°C ambient temperature unless otherwise specified.)

参数 Parameters	符号 Symbol	数值 Value	单位 Unit
Collector-Base Voltage	V _{CBO}	-40	V
Collector-Emitter Voltage	V _{CEO}	-25	V
Emitter -Base Voltage	V _{EBO}	-5	V
Collector Current-Continuous	I _C	-1500	mA
Collector Power Dissipation	P _C	300	mW
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55-+150	°C
Thermal resistance From junction to ambient	R _{θJA}	417	°C/W

电特性 (TA = 25°C 除非另有规定)

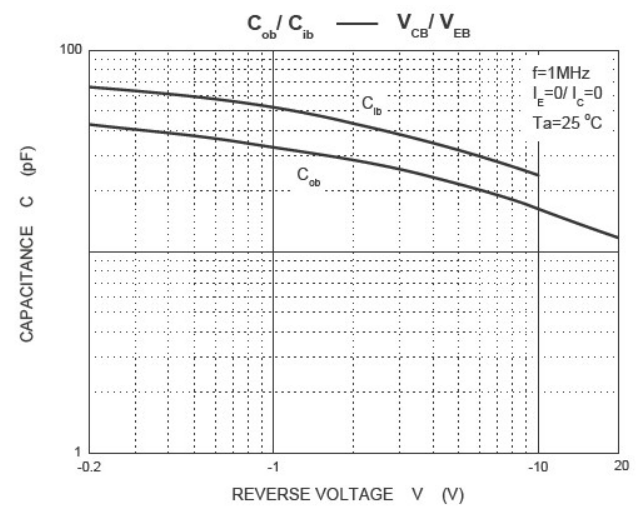
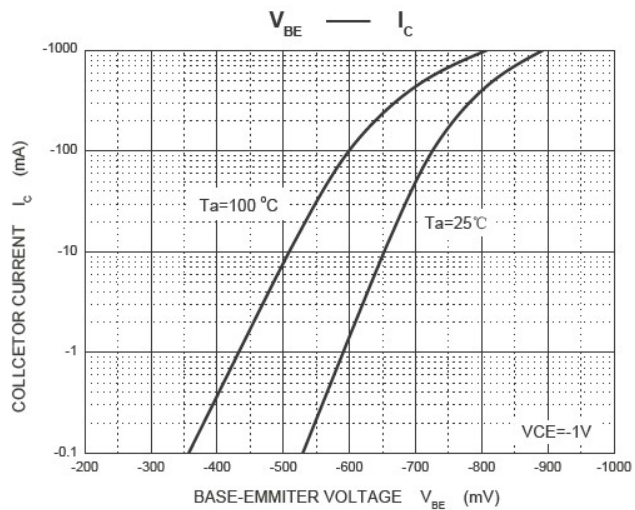
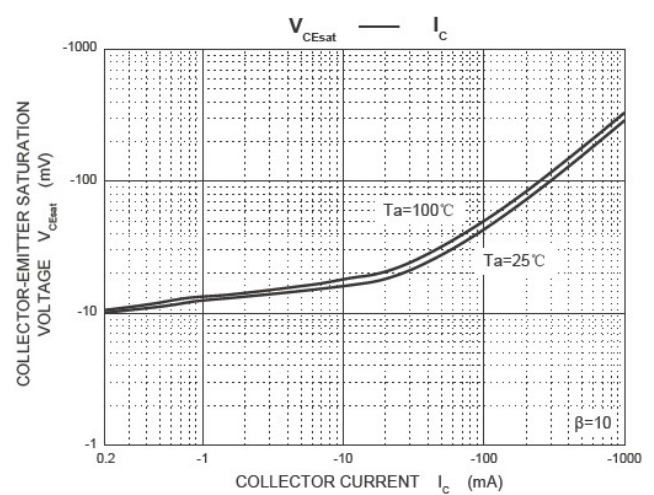
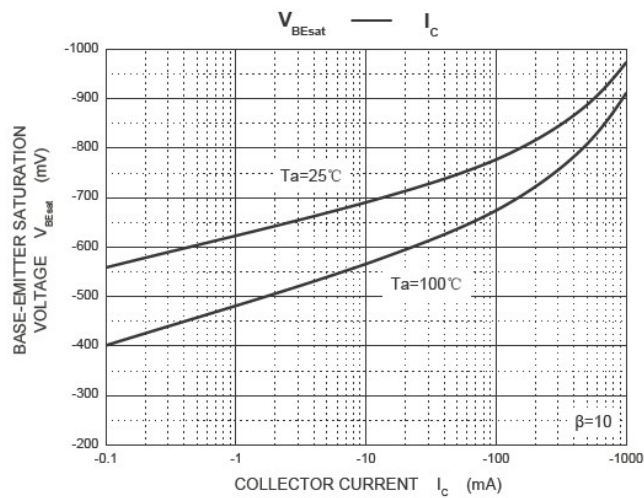
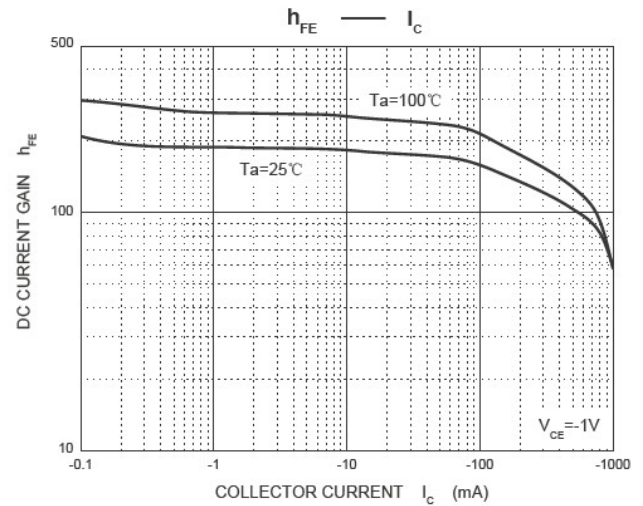
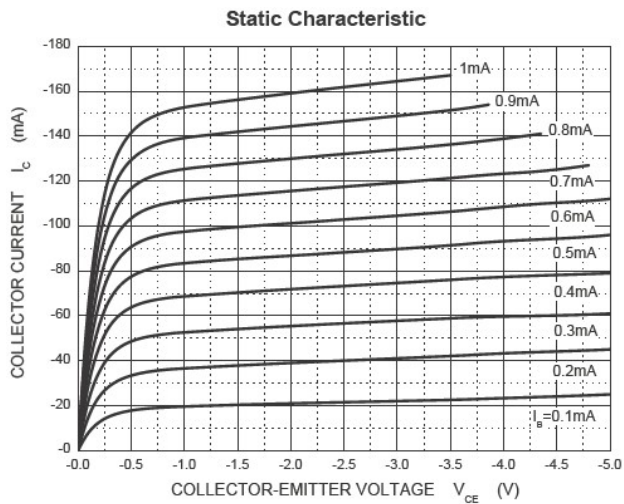
Electrical Characteristics (Ratings at 25°C ambient temperature unless otherwise specified).

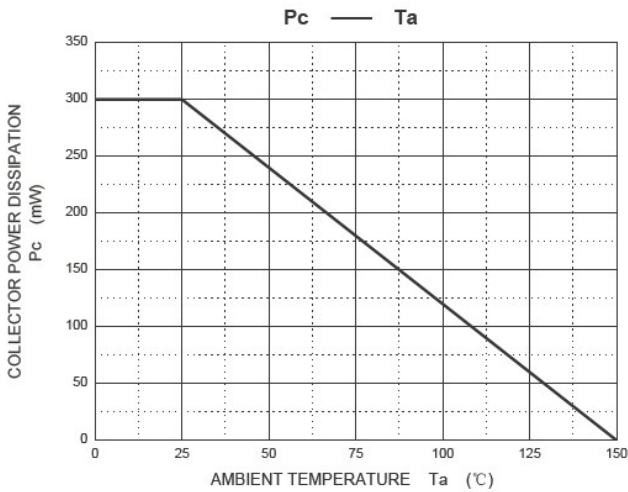
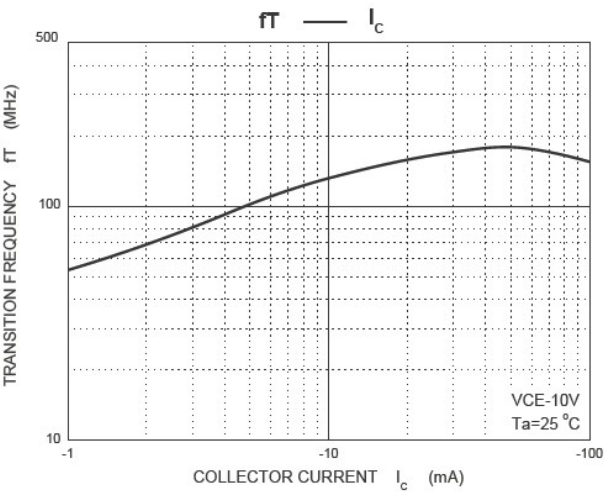
参数 Parameter	符号 Symbols	测试条件 Test Condition	界限 Limits		单位 Unit
			Min	Max	
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100uA, I _E =0	-40		V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-0.1mA, I _B =0	-25		V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-100uA, I _C =0	-5		V
Collector cut-off current	I _{CBO}	V _{CB} =-40V, I _E =0		-100	nA
Collector cut-off current	I _{CEO}	V _{CE} =-20V, I _B =0		-100	nA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0		-100	nA
DC current gain	h _{FE} (1)	V _{CE} =-1V, I _C =-100mA	120	400	
	h _{FE} (2)	V _{CE} =-1V, I _C =-800mA	40		
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-800mA, I _B =-80mA		-0.50	V
Base -emitter saturation voltage	V _{BE(sat)}	I _C =-800mA, I _B =-80mA		-1.20	V
Base-emitter voltage	V _{BE}	V _{CE} =-1V, I _C =-10mA		-1.00	V
Transition frequency	f _T	V _{CE} =-10V, I _C =-50mA, f=30MHz	100		MHz
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz		20	pF

CLASSIFICATION OF h_{FE}(1)

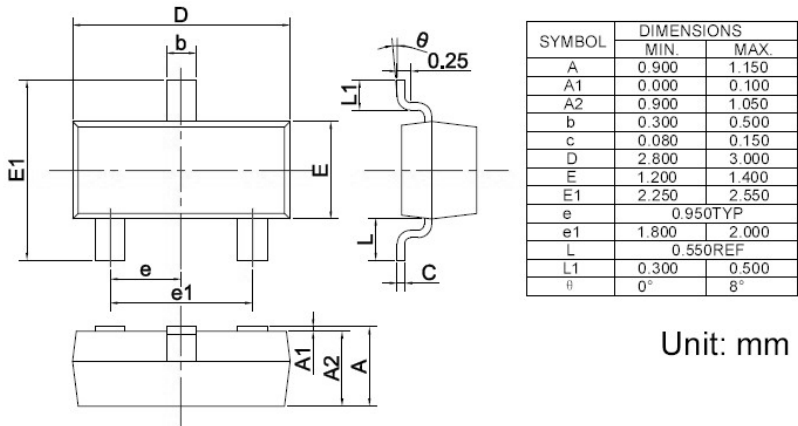
RANK	L	H	J
RANGE	120-200	200-350	300-400

Typical characteristics

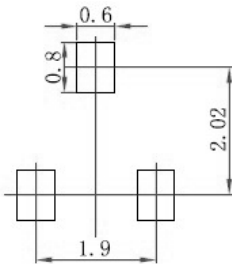




SOT-23 PACKAGE OUTLINE Plastic surface mounted package



焊盘设计参考Precautions: PCB Design
Recommended land dimensions for SOT-23 diode. Electrode patterns for PCBs



Note:
1.Controlling dimension:In millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.